

제22회 한국반도체학술대회

2015년 2월 10일(화) - 12일(목), 인천 송도컨벤시아

F. Silicon Device and Integration Technology 분과

Room G

1F / 109호

2015년 2월 12일(목) 14:50-16:20

[TG3-F] Processes and Test Methodologies for Scaled CMOS

좌장: 이성주 (성균관대학교), 조성재 (가천대학교)

TG3-F-1	14:50-15:05	TDR 분석법을 이용한 미세전계효과소자의 Effective Mobility 추출 방법 김용훈, 정욱진, 강수철, 이영근, 이병훈 Center for Emerging Electric Devices and Systems, School of Material Science and Engineering, Gwangju Institute of Science and Technology
TG3-F-2	15:05-15:20	In-situ Thermal Annealing and ALD SiO₂ Interfacial Layer as an Interface Passivation for Ge pMOSFETs Min-Ho Kang ^{1,2} , Ho-Ryeong Lee ¹ , Jae-Sub Oh ² , Je-Young Kim ¹ , Ga-Won Lee ¹ , and Hi-Deok Lee ¹ ¹ Department of Electronics Engineering, Chungnam National University, ² Division of Nano-Process Division, National NanoFab Center
TG3-F-3	15:20-15:35	Electrical Characteristics of MOSCAP with High-κ/Metal Gateusing an Oxygen Scavenging Process Junil Lee, Hyun Woo Kim, Jang Hyun Kim, Euyhwan Park, Dae Woong Kwon, Tae-Hyung Park, and Byung-Gook Park Department of Electrical and Computer Engineering, Seoul National University
TG3-F-4	15:35-15:50	A Novel Processing Technique for Reducing Contact Resistance of n⁺ Si Junctions by a High-κ Dielectric Prepared by Atomic Layer Deposition Jeongmin Lee ¹ , Seung Wook Ryu ² , Seongmin Lee ¹ , Sungjun Kim ³ , Seongjae Cho ^{1,4} , Hyeong Joon Kim ² , and Byung-Gook Park ³ ¹ Department of IT Convergence Engineering and ⁴ Department of Electronic Engineering, Gachon University, ² Department of Materials Science and Engineering, Seoul National University, ³ Department of Electrical and Computer Engineering, Seoul National University
TG3-F-5	15:50-16:05	Ni-Al Alloy Silicide to Reduce the Electron Schottky Barrier Height in Source/Drain Junction for High Performance Nano-Scale NMOSFET Horyeong Lee, Meng Li, Jeyoung Kim, Ga-Won Lee, and Hi-Deok Lee Department of Electronics Engineering, Chungnam National University
TG3-F-6	14:25-14:40	2-Dimensional Defect Monitoring Array with Series Testing Chin Kim, In Wook Oh, Jae Seok Yang, Jong Hyun Lee, and Sun Hom Paak Samsung Electronics Co., Ltd.